

Attorney Docket No. 0756-7218

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Shunpei YAMAZAKI et al.

Serial No. 10/712,062

Filed: November 14, 2003

For: SEMICONDUCTOR DEVICE AND
METHOD OF FABRICATING SAME

) Group Art Unit: 2826

) Examiner: Fetsum Abraham

) CERTIFICATE OF MAILING) I hereby certify that this correspondence is
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Commissioner for Patents, P.O. Box 1450,
Alexandria, VA 22313-1450, on 2.8.06

INFORMATION DISCLOSURE STATEMENTHonorable Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing information known to Applicant and requests that this information be made of record in the above identified application. Copies are submitted herewith in accordance with 37 C.F.R. 1.98(a).

Copies of U.S. patents and U.S. publications are not enclosed in accordance with the Notice published in the Official Gazette on August 5, 2003 entitled *Information Disclosure Statements May Be Filed Without Copies of U.S. Patents and Published Applications in Patent Applications filed after June 30, 2003*, which waives the requirement under 37 CFR 1.98(a)(2)(i) for submitting a copy of each cited U.S. patent and each U.S. publication.

This Information Disclosure Statement is being submitted with an RCE. Therefore, no fee is required.

Respectfully submitted,

Eric J. Robinson
Reg. No. 38,285
Robinson Intellectual Property Law Office, P.C.
PMB 955
21010 Southbank Street
Potomac Falls, Virginia 20165
(571) 434-6789

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BTL/

PTO/SB/08A (08-00)

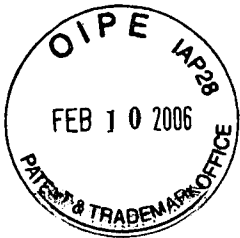
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U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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CORRECTION TO PREVIOUSLY SUBMITTED INFORMATION DISCLOSURE
STATEMENT

Honorable Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

It has come to applicant's attention that an Information Disclosure Statement previously submitted included inadvertent typographical errors or incomplete information.

Specifically, the Information Disclosure Statement filed November 14, 2003 included the following inaccuracies:

- 1) U.S. Patent 4,330,363 was incorrectly listed with the inventor as Biefesen et al. The correct inventor should be Biegesen et al.;
- 2) U.S. Patent 4,996,077 was incorrectly listed with the inventor as Mosiehi et al. The correct inventor should be Moslehi et al.
- 3) U.S. Patent No. 5,089,441 is incorreceted lised with the inventor as Mosiehi et al. The correct inventor should be Moslehi et al.
- 4) EP 0 178 447 was incorrectly listed with a publication date of 10/09/84. The correct publication date is 04/23/1986.
- 5) The article to Kruper et al. did not include the volume and number. The corrected citation should read: Kuper et al., "Effects of Fluorine Implantation on the

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Kinetics of Dry Oxidation of Silicon," Volume 60, No. 3, August 1, 1986, pp. 985-990, J. Applied Physics.

6) The article to Nemanich et al. incorrectly lists the volume. The correct volume number is 23.

7) The article to Wolf et al. did not include the volume. The corrected citation should read: Wolf et al., "Thermal Oxidation of Single Crystal Silicon," Volume 1, 1986, pp. 207-211, Silicon Processing for the VLSI Era.


8) The article to Dvurechenskii et al. did not include the volume. The corrected citation should read: Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals," Volume 95, 1986, pp. 635-640, Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR.

9) The article to Hayzelden et al. incorrectly lists the date as May 15, 1993. The correct date is June 1, 1993.

10) Page 5 and 10 of the Information Disclosure Statement have been initialed by the Examiner and dated "8/30/01." The subject application was filed on November 14, 2003, and therefore the date of review of incorrect. Copies are enclosed.

The above inaccuracies are corrected on the 1449 Form attached hereto. This *Correction to Previously Submitted Information Disclosure Statements* is being submitted herewith with an Information Disclosure Statement, RCE, and requisite fee. The Examiner is requested to initial the attached PTO Form 1449 evidencing consideration of the above references and line through these references on the previously submitted Information Disclosure Statements to ensure that the correct information is printed correctly on any issued patent.

Respectfully submitted,


Eric J. Robinson
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	10/712,062
				Filing Date	November 14, 2003
				First Named Inventor	Shunpei YAMAZAKI et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham Benjamin T. Liu
Sheet	1	of	1	Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
/BTL/		4,330,363		Biegesen et al.	05/18/1982	
↓		4,996,077		Moslehi et al.	02/26/1991	
		5,089,441		Moslehi	02/18/1992	

FOREIGN PATENT DOCUMENTS								
Examiner Initials	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
/BTL/		EP	0 178 447			04/23/1986		Eng.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
/BTL/		Kuper et al., "Effects of Fluorine Implantation on the Kinetics of Dry Oxidation of Silicon," Volume 60, No. 3, August 1, 1986, pp. 985-990, J. Applied Physics.	
↓		Nemanich et al., "Structure and Growth of the Interface of Pd on a-SiH ₃ ," June 15, 1981, pp. 6828-6831, The American Physical Society Physics Review, Vol. 23, No. 12.	
		Wolf et al., "Thermal Oxidation of Single Crystal Silicon," Volume 1, 1986, pp. 207-211, Silicon Processing for the VLSI Era.	
		Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals," Volume 95, 1986, pp. 635-640, Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR.	
↓		Hayzelden et al., "Silicide Formation and Silicide Mediated Crystallization of Nickel- Implanted Amorphous Silicon Thin Films," June 1, 1993, pp. 8279-8289, J. Appl. Phys. 73(12)	
Examiner Signature	/Benjamin Tzu-Hung Liu/		Date Considered
			05/01/2008

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known		
				Application Number	Based on 10/214,691	
Sheet		5	of	12	Attorney Docket Number	0756-7218
Filing Date		August 9, 2002				
First Named Inventor		Shunpei YAMAZAKI, et al.				
Group Art Unit		2826				
Examiner Name		Fetsum Abraham				

U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
✓		6,013,929		Ohtani	01/11/00	
		6,048,758		Yamazaki et al.	04/11/00	
		6,063,654		Ohtani	05/16/00	
		6,077,731		Yamazaki et al.	06/20/00	
		6,093,934		Yamazaki et al.	07/25/00	
		6,100,562		Yamazaki et al.	08/08/00	
		RE 28,385		Mayer	04/08/75	
		RE 28,386		Heiman et al.	04/08/75	

FOREIGN PATENT DOCUMENTS							
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		Office ³	Number ⁴	Kind Code ³ (if known)			
✓		EP	0 178 447			10/09/84	English
		JP	01-187814			07/27/89	Full
		JP	01-187874			07/27/89	Abst.
		JP	01-187875			07/27/89	Abst.
		JP	01-206632			08/18/89	Abst.
		JP	02-140915			05/30/90	Full
		JP	02-148687			06/07/90	Abst.
		JP	02-275641			11/09/90	Abst.
		JP	03-280418			12/11/91	Abst.
		JP	03-280420			12/11/91	Full
		JP	05-082442			04/02/93	Abst.
		JP	05-107561			04/30/93	Abst.
		JP	05-299348			11/12/93	Abst.
		JP	06-232059			08/19/94	Full
		JP	07-161634			06/23/95	Abst.
		JP	07-321339			12/08/95	Abst.
		JP	08-129358			05/21/96	Abst.
		JP	08-129359			05/21/96	Abst.
		JP	08-129360			05/21/96	Abst.
		JP	08-234683			09/13/96	Abst.
		JP	08-241047			09/17/96	Abst.
		JP	08-241048			09/17/96	Abst.
		JP	08-241057			09/17/96	Abst.
		JP	08-241997			09/17/96	Abst.
		JP	60-105216			06/10/85	Full
		JP	61-063017			04/01/86	Full
		JP	61-063107			04/01/86	Abst.
		JP	62-169356			07/25/87	Abst.

Examiner Signature	8/30/01	Date Considered	8/30/01
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
Sheet	10	of	12	Attorney Docket Number	0756-7218

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		Number	Kind Code ³ (if known)			
77		5,403,772		Zhang et al.	04/04/95	
		5,426,064		Zhang et al.	06/20/95	
		5,481,121		Zhang et al.	01/02/96	
		5,488,000		Zhang et al.	01/30/96	
		5,492,843		Adachi et al.	02/20/96	
		5,501,989		Takayama et al.	03/26/96	
		5,508,533		Takemura	04/16/96	
		5,529,937		Zhang et al.	06/25/96	
		5,534,716		Takemura	07/09/96	
		5,543,352		Ohtani et al.	08/06/96	
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		5,569,610		Zhang et al.	10/29/96	
		5,569,936		Zhang et al.	10/29/96	
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		5,604,360		Zhang et al.	02/18/97	
		5,605,846		Ohtani et al.	02/25/97	
		5,606,179		Yamazaki et al.	02/25/97	
		5,608,232		Yamazaki et al.	03/04/97	
		5,612,250		Ohtani et al.	03/18/97	
		5,614,426		Funada et al.	03/25/97	
		5,614,733		Zhang et al.	03/25/97	
		5,616,506		Takemura	04/01/97	
		5,620,910		Teramoto	04/15/97	
		5,621,224		Yamazaki et al.	04/15/97	
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		5,637,515		Takemura	06/10/97	
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		5,643,826		Ohtani et al.	07/01/97	
		5,646,424		Zhang et al.	07/08/97	
		5,654,203		Ohtani et al.	08/05/97	
		5,656,825		Kusumoto et al.	08/12/97	
		5,663,077		Adachi et al.	09/02/97	
		5,677,549		Takayama et al.	10/14/97	
		5,696,386		Yamazaki	12/09/97	
		5,696,388		Funada et al.	12/09/97	
		5,700,333		Yamazaki et al.	12/23/97	

Examiner Signature	<i>Fet Hsueh</i>	Date Considered	8/30/01
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